

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q80166

Masato KOBAYAKAWA, et al.

Appln. No.: 10/589,610

Group Art Unit: 2818

Confirmation No.: 8635

Examiner: Ngan V. NGO

Filed: August 16, 2006

For: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER  
STRUCTURE AND PRODUCTION METHOD THEREOF

**AMENDMENT UNDER 37 C.F.R. § 1.111**

**MAIL STOP AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated April 10, 2008, please amend the above-identified application as follows on the accompanying pages.

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